

DATA SHEET

BFG197; BFG197/X; BFG197/XR NPN 7 GHz wideband transistor

Product specification
Supersedes data of November 1992
File under discrete semiconductors, SC14

1995 Sep 13

NPN 7 GHz wideband transistor

BFG197; BFG197/X; BFG197/XR

FEATURES

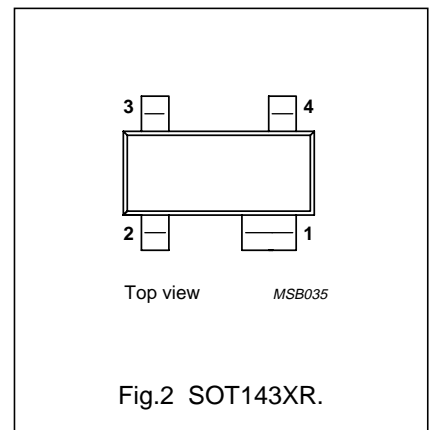
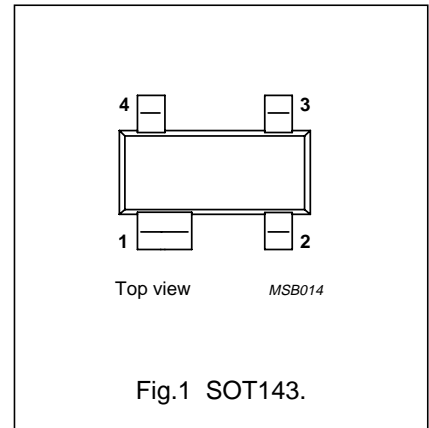
- High power gain
- Low noise figure
- Gold metallization ensures excellent reliability.

DESCRIPTION

The BFG197 is a silicon NPN transistor in a 4-pin, dual-emitter plastic SOT143 envelope. It is primarily intended for wideband applications in the GHz range, such as satellite TV systems and repeater amplifiers in fibre-optic systems.

PINNING

PIN	DESCRIPTION
BFG197 (Fig.1) Code: V5	
1	collector
2	base
3	emitter
4	emitter
BFG197/X (Fig.1) Code: V13	
1	collector
2	emitter
3	base
4	emitter
BFG197A/XR (Fig.2) Code: V35	
1	collector
2	emitter
3	base
4	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	10	V
I_C	collector current	DC value	–	–	100	mA
P_{tot}	total power dissipation	up to $T_s = 75\text{ °C}$; note 1	–	–	350	mW
C_{re}	feedback capacitance	$I_C = i_c = 0$; $V_{CB} = 8\text{ V}$; $f = 1\text{ MHz}$	–	0.85	–	pF
f_T	transition frequency	$I_C = 50\text{ mA}$; $V_{CE} = 4\text{ V}$; $f = 2\text{ GHz}$	–	7.5	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 50\text{ mA}$; $V_{CE} = 6\text{ V}$; $T_{amb} = 25\text{ °C}$; $f = 1\text{ GHz}$	–	16	–	dB
		$I_C = 50\text{ mA}$; $V_{CE} = 6\text{ V}$; $T_{amb} = 25\text{ °C}$; $f = 2\text{ GHz}$	–	10	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 15\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ °C}$; $f = 1\text{ GHz}$	–	1.7	–	dB

Note

1. T_s is the temperature at the soldering point of the collector tab.

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	20	V
V _{CEO}	collector-emitter voltage	open base	–	10	V
V _{EBO}	emitter-base voltage	open collector	–	2.5	V
I _C	collector current	DC value, continuous	–	100	mA
P _{tot}	total power dissipation	up to T _s = 75 °C; note 1	–	350	mW
T _{stg}	storage temperature range		–65	+150	°C
T _j	junction operating temperature		–	175	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-s}	from junction to soldering point; note 1	290	K/W

Note

1. T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

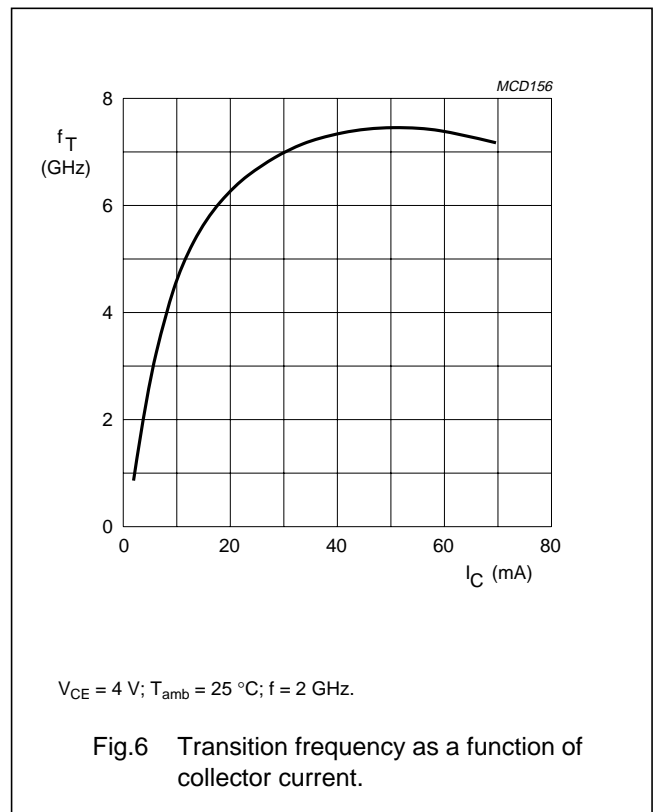
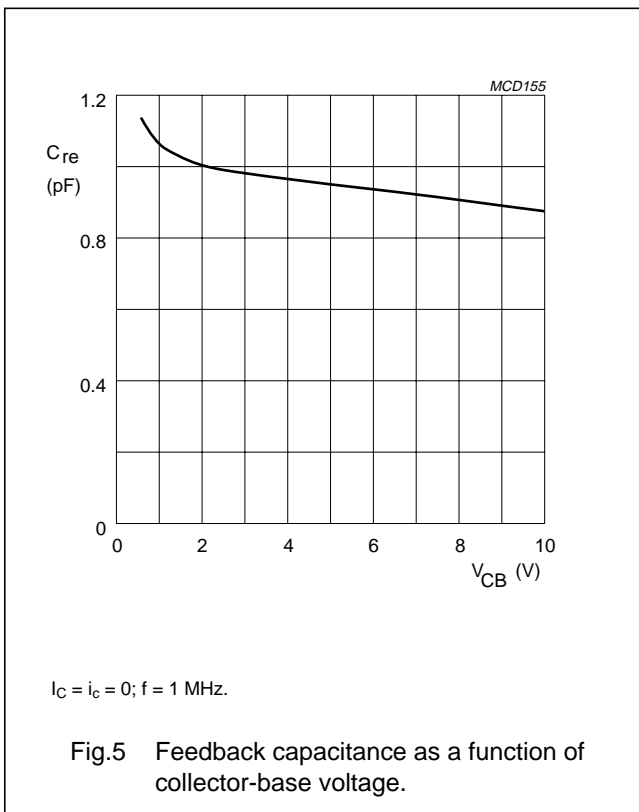
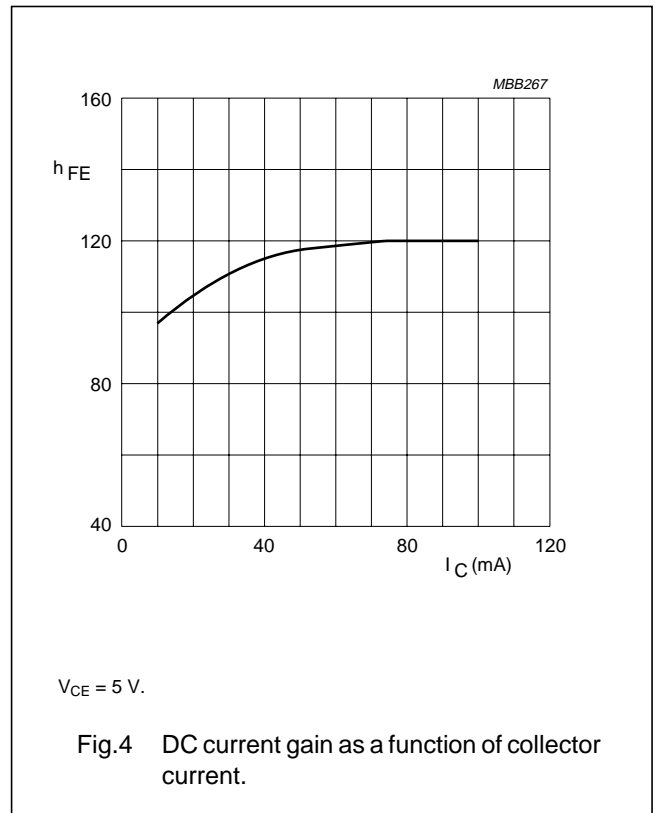
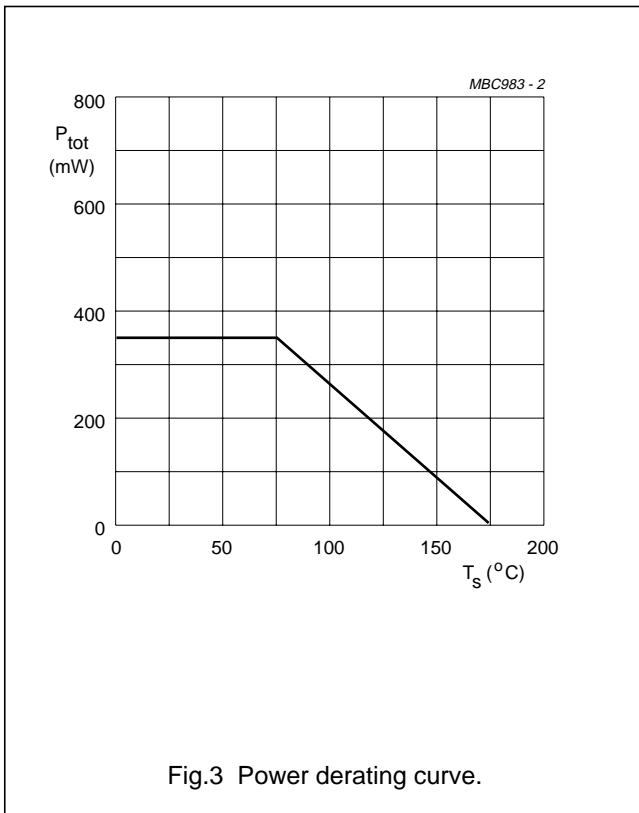
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector leakage current	I _E = 0; V _{CB} = 5 V	–	–	100	nA
h _{FE}	DC current gain	I _C = 50 mA; V _{CE} = 5 V	40	110	–	
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 8 V; f = 1 MHz	–	1.5	–	pF
C _e	emitter capacitance	I _C = i _c = 0; V _{EB} = 0.5 V; f = 1 MHz	–	3.3	–	pF
C _{re}	feedback capacitance	I _C = i _c = 0; V _{CB} = 8 V; f = 1 MHz	–	0.85	–	pF
f _T	transition frequency	I _C = 50 mA; V _{CE} = 4 V; f = 2 GHz	–	7.5	–	GHz
G _{UM}	maximum unilateral power gain (note 1)	I _C = 50 mA; V _{CE} = 6 V; T _{amb} = 25 °C; f = 1 GHz	–	16	–	dB
		I _C = 50 mA; V _{CE} = 6 V; T _{amb} = 25 °C; f = 2 GHz	–	10	–	dB
F	noise figure	Γ _s = Γ _{opt} ; I _C = 15 mA; V _{CE} = 8 V; T _{amb} = 25 °C; f = 1 GHz	–	1.7	–	dB
		Γ _s = Γ _{opt} ; I _C = 50 mA; V _{CE} = 6 V; T _{amb} = 25 °C; f = 2 GHz	–	2.3	–	dB
d ₂	second order intermodulation distortion	V _{CE} = 6 V; V _o = 50 dBmV;	–	–51	–	dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming S₁₂ is zero and $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$ dB.

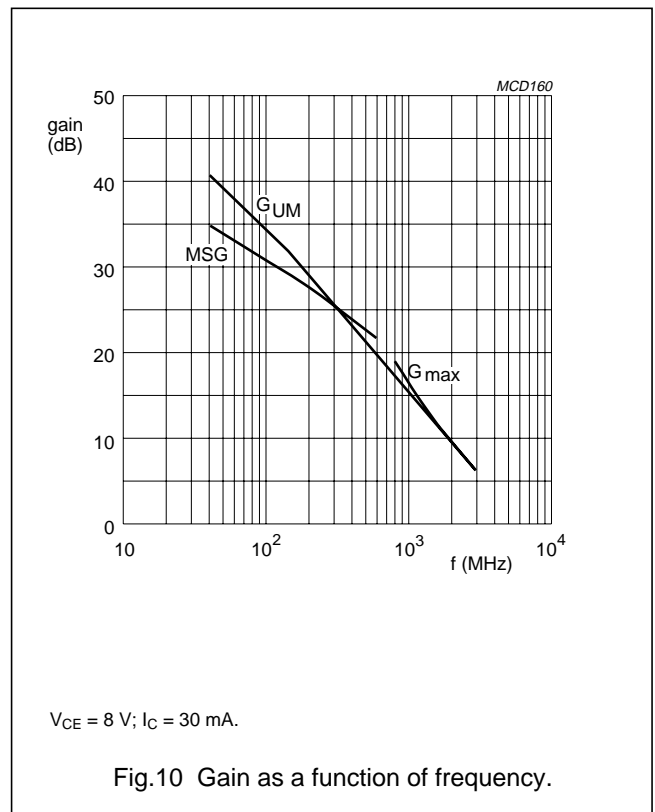
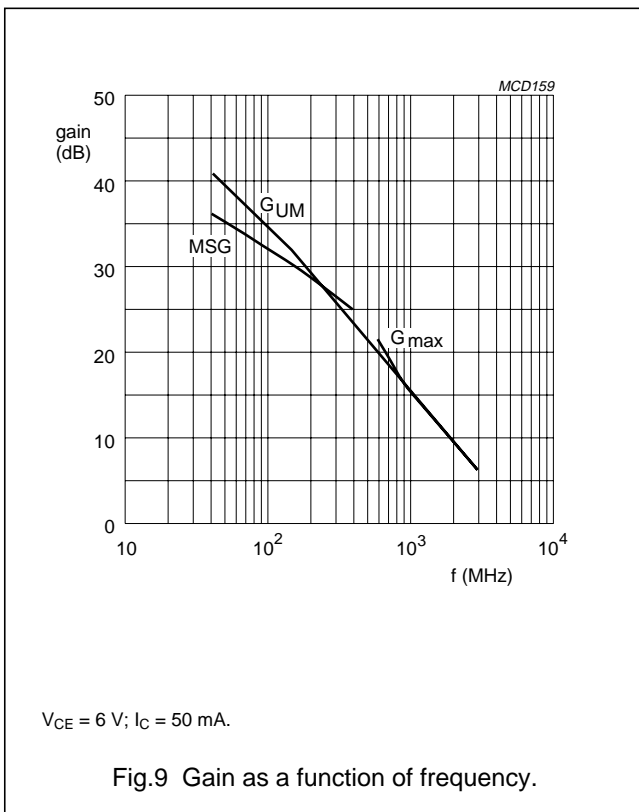
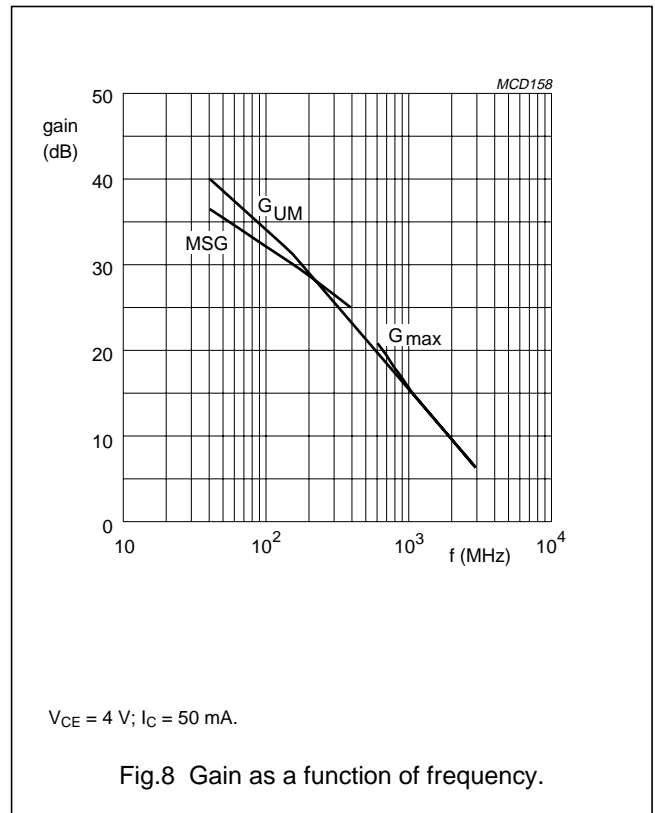
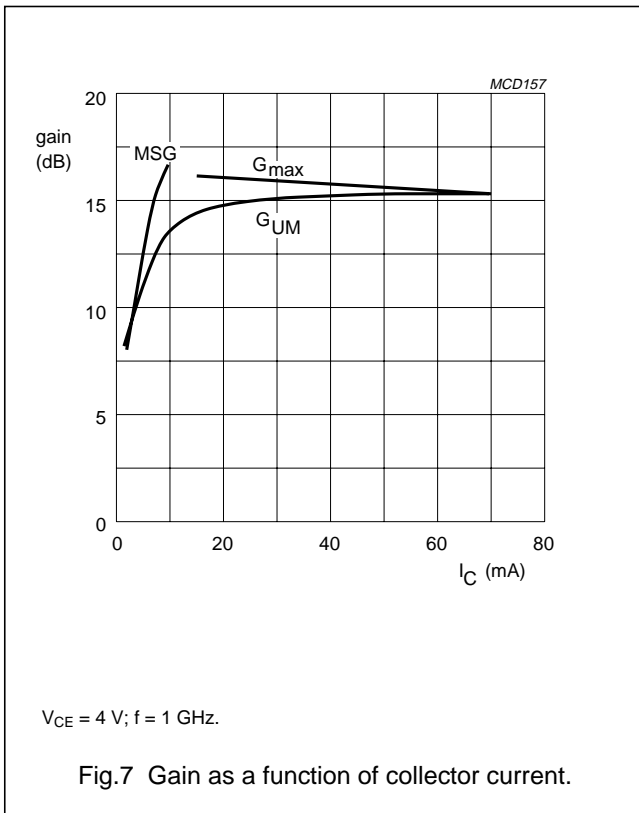
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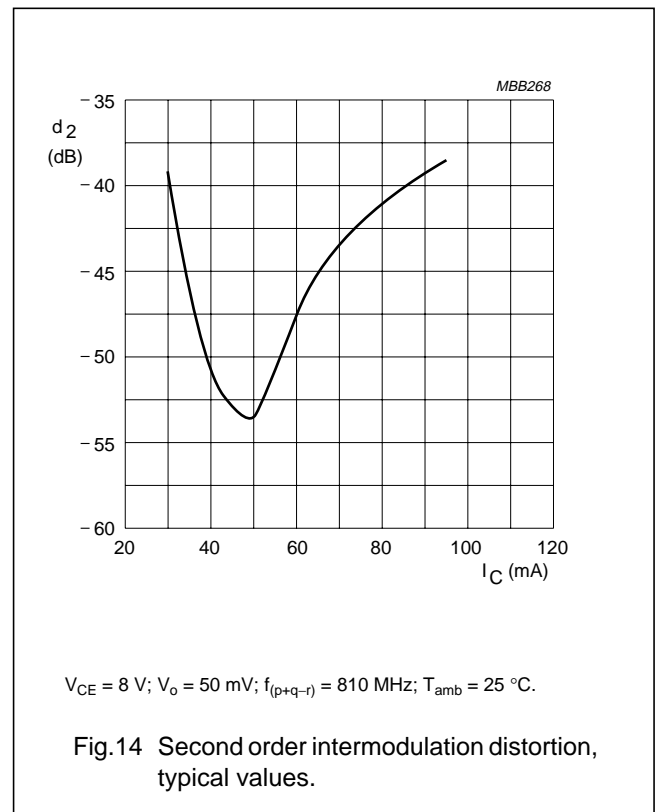
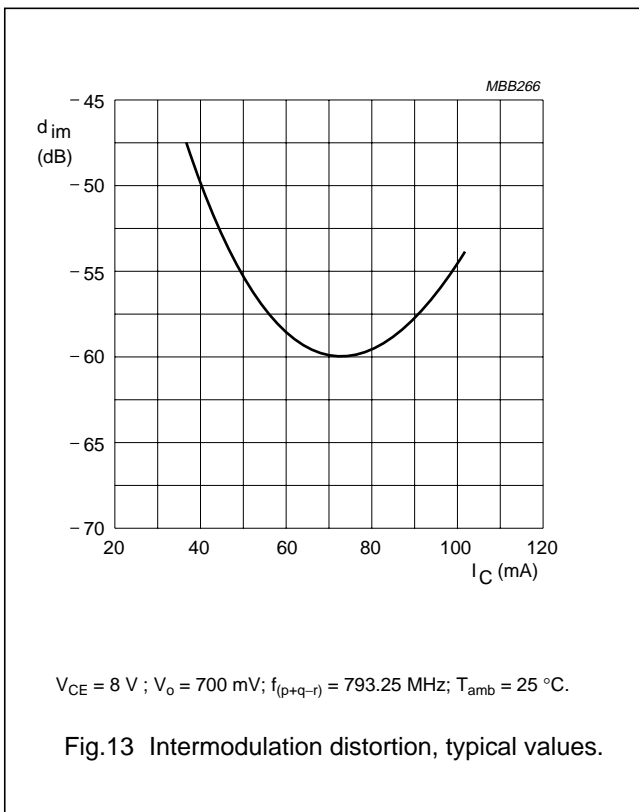
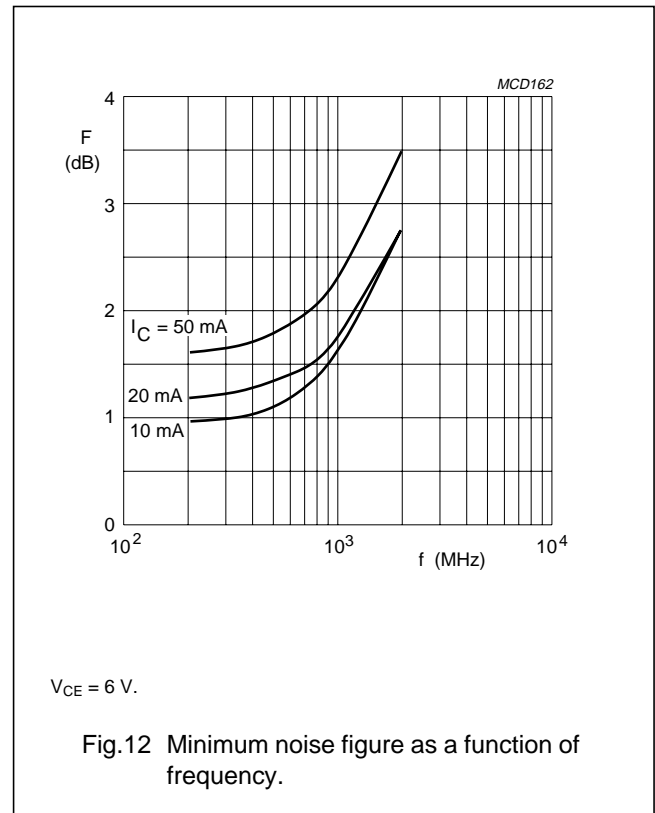
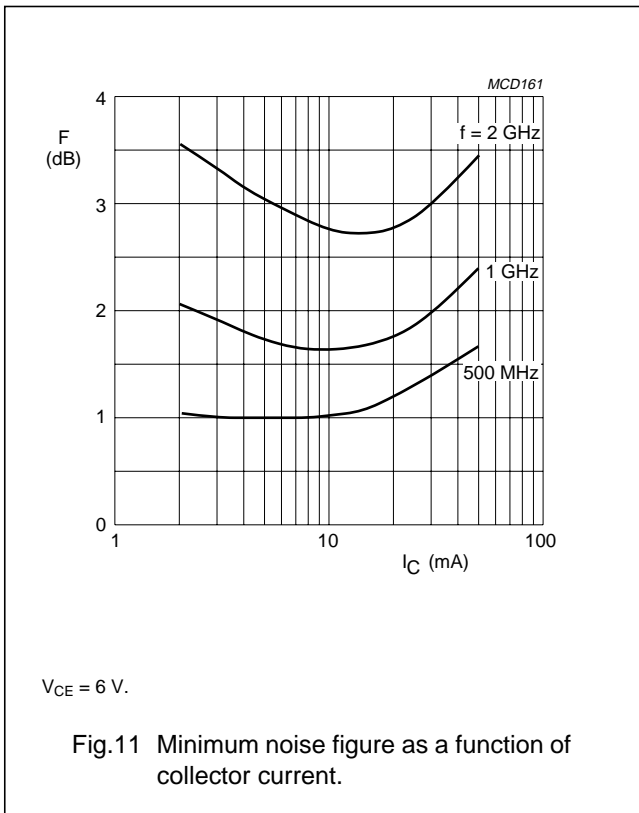
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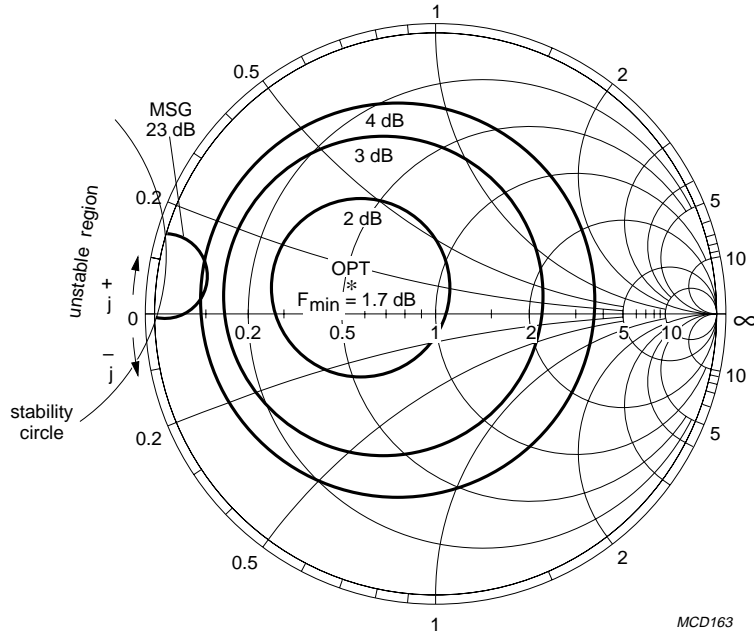
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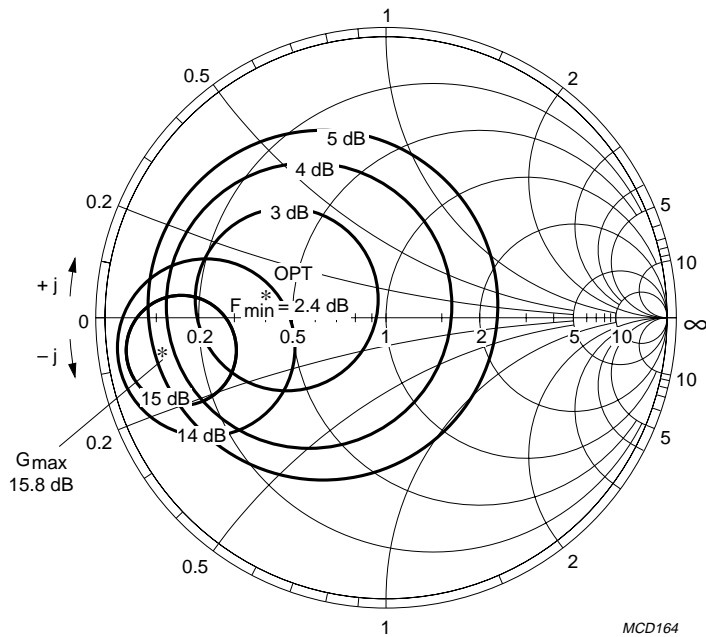
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$Z_0 = 50 \Omega$.
Maximum stable gain = 23 dB.

Fig.15 Noise circle figure.

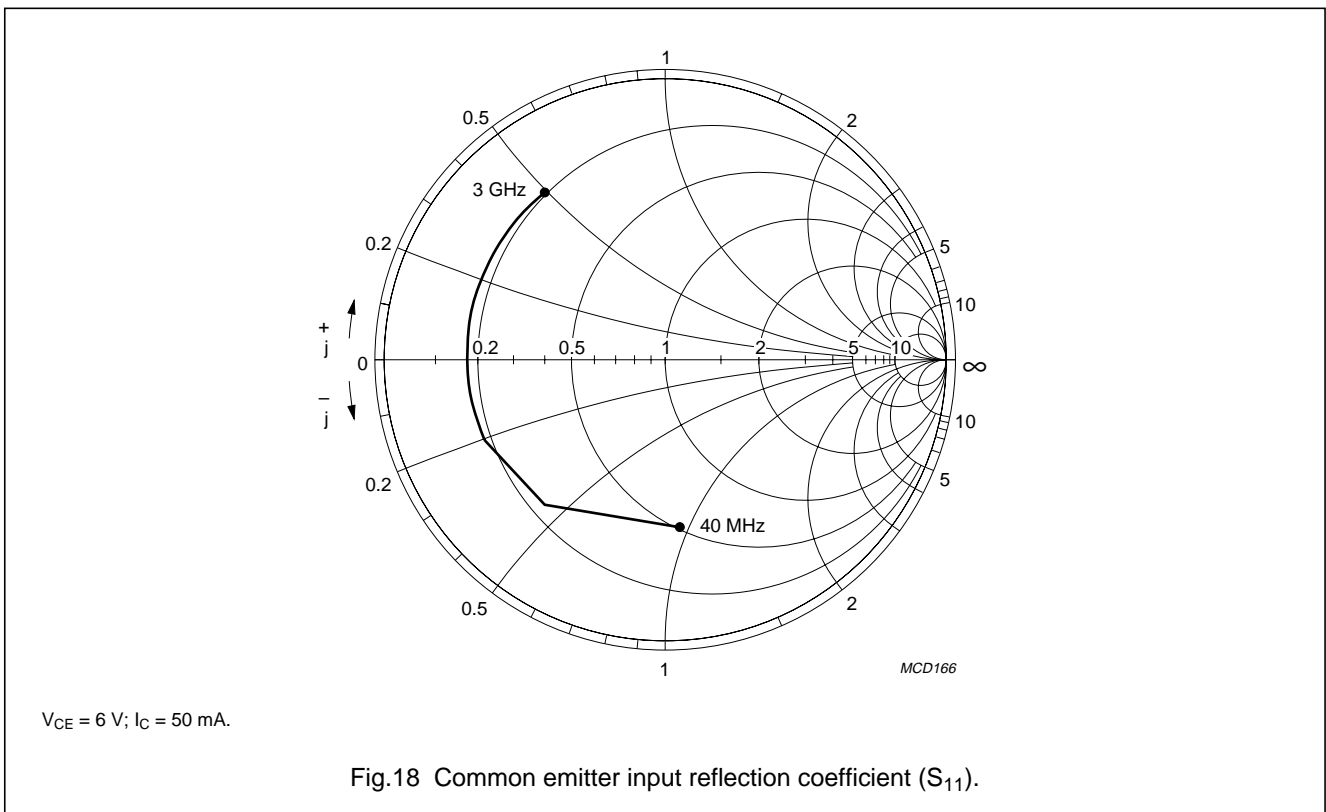
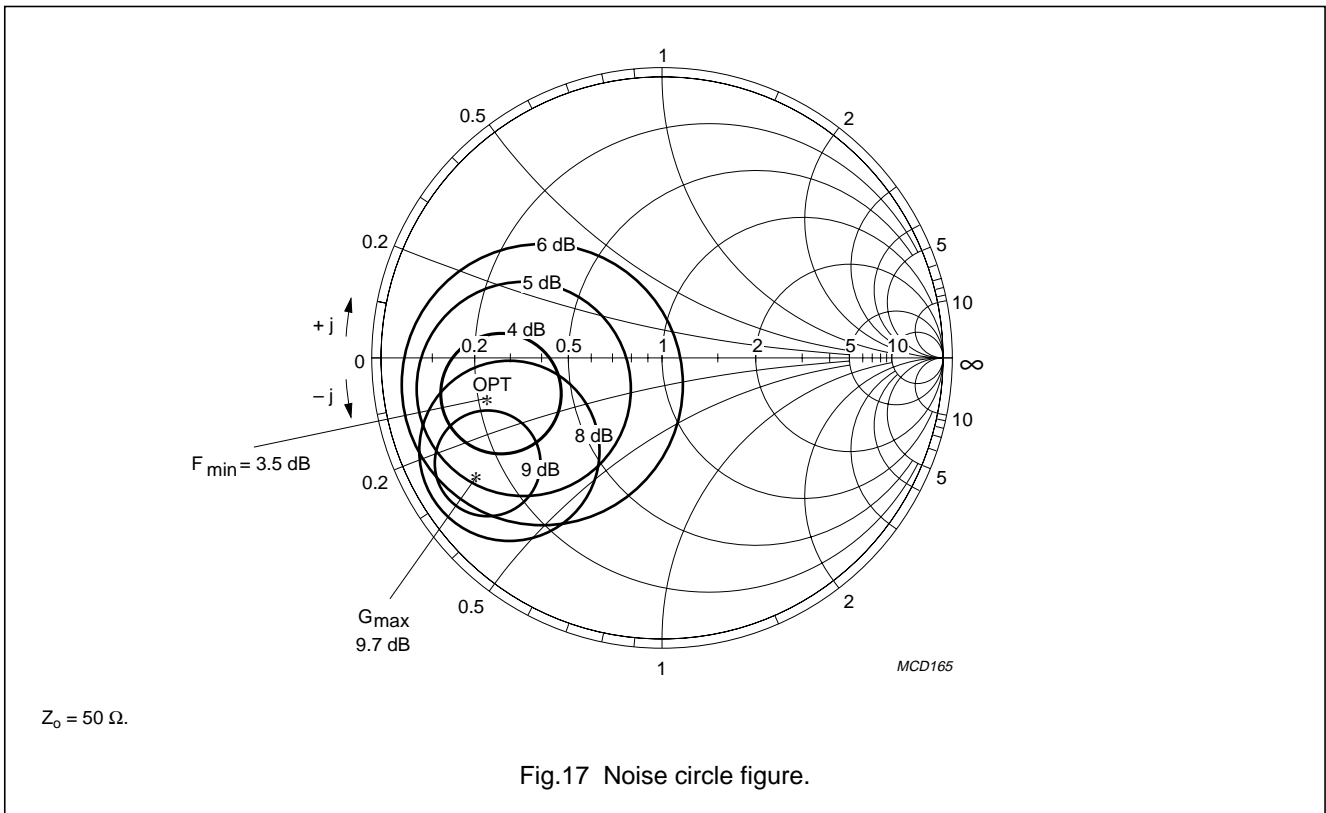


$Z_0 = 50 \Omega$.

Fig.16 Noise circle figure.

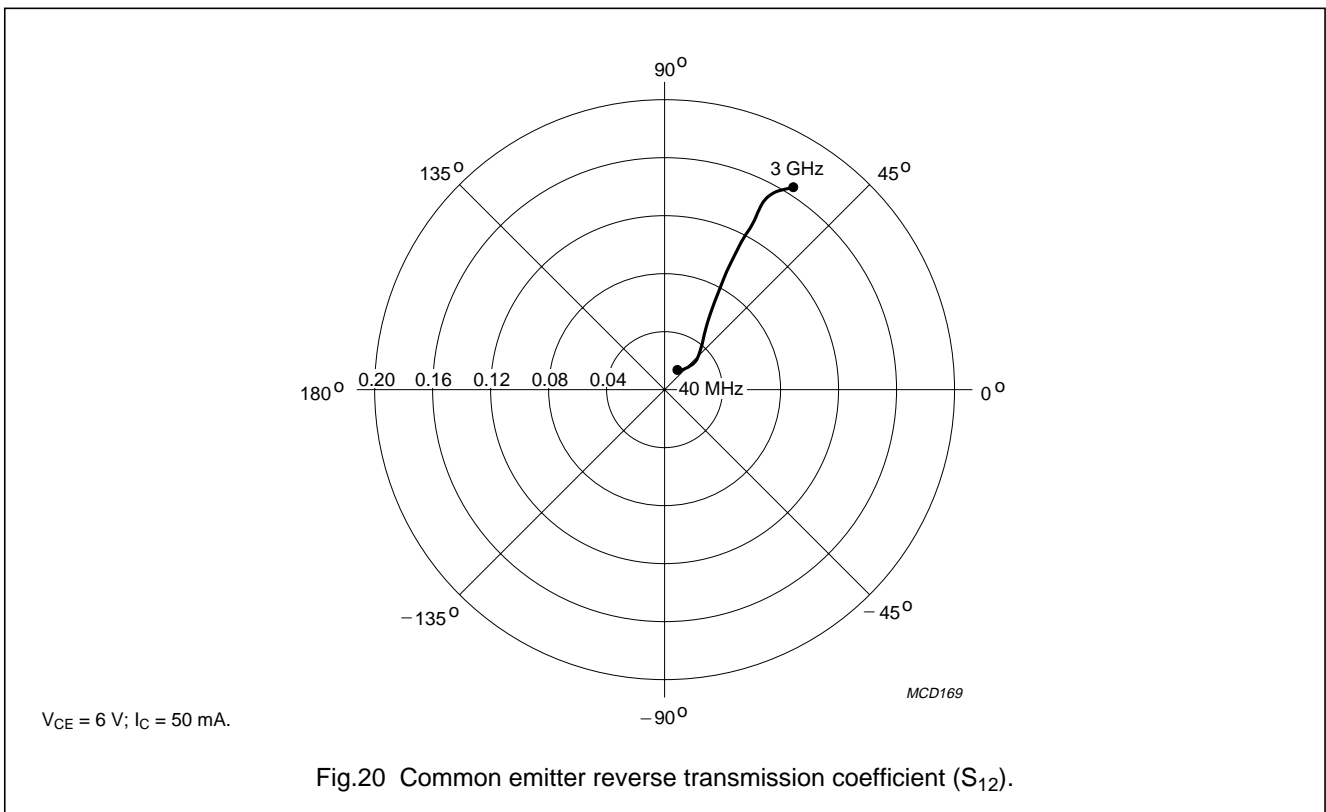
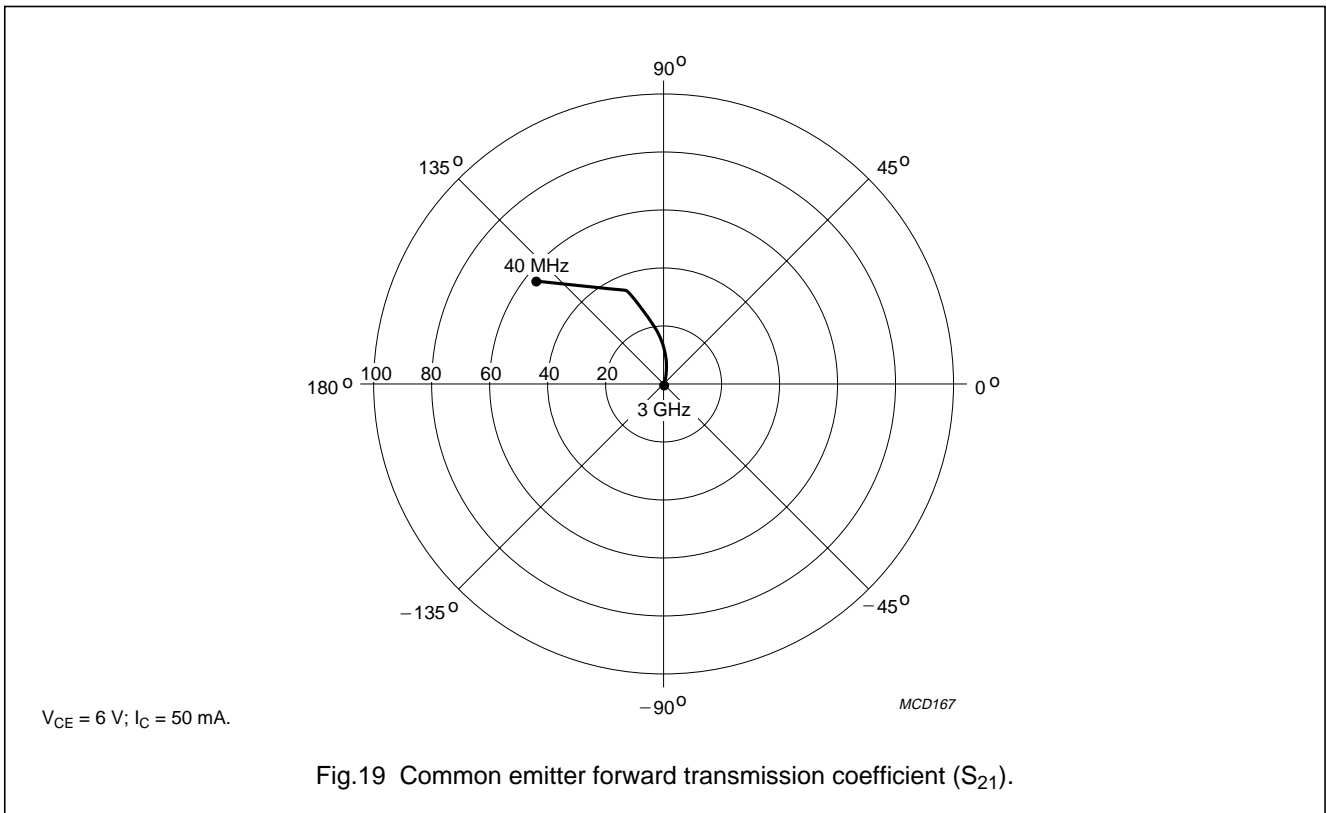
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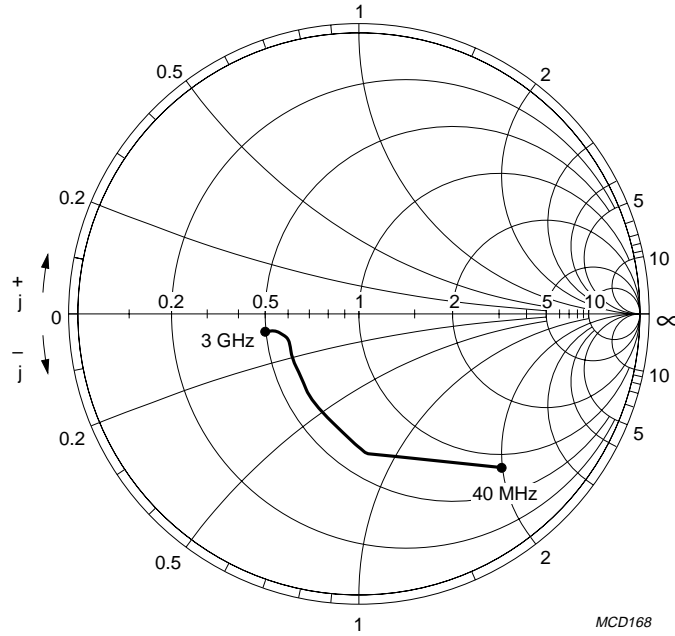
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$V_{CE} = 6\text{ V}; I_C = 50\text{ mA}$.

Fig.21 Common emitter output reflection coefficient (S_{22}).

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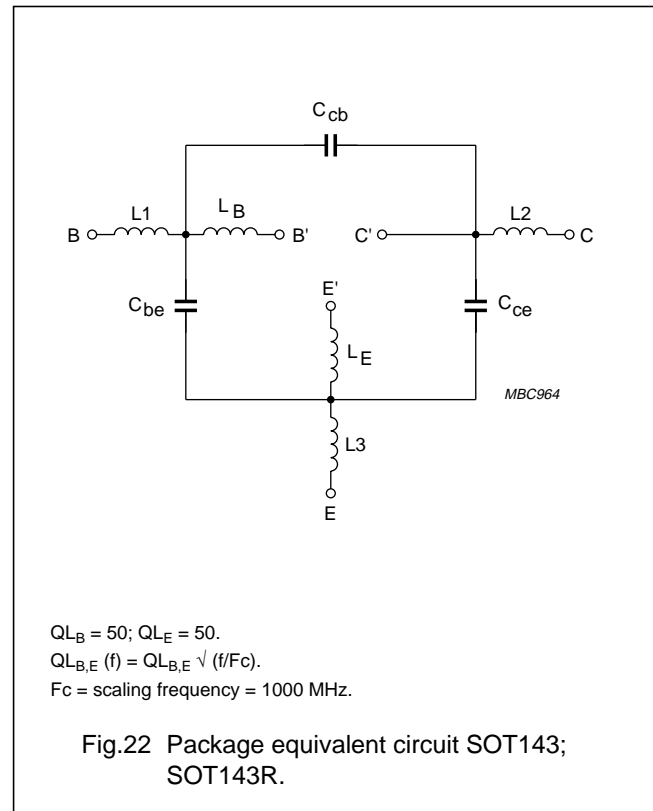
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SPICE parameters for BFQ195 crystal

SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	1.972	fA
2	BF	150.0	–
3	NF	990.8	m
4	VAF	54.72	V
5	IKF	30.00	A
6	ISE	47.82	fA
7	NE	1.580	–
8	BR	165.4	–
9	NR	993.9	m
10	VAR	2.351	V
11	IKR	9.967	A
12	ISC	3.510	aA
13	NC	1.124	–
14	RB	5.000	Ω
15	IRB	1.000	μA
16	RBM	5.000	Ω
17	RE	368.1	mΩ
18	RC	937.2	mΩ
19 (note 1)	XTB	0.000	–
20 (note 1)	EG	1.110	EV
21 (note 1)	XTI	3.000	–
22	CJE	3.388	pF
23	VJE	600.0	mV
24	MJE	302.9	m
25	TF	11.06	ps
26	XTF	30.02	–
27	VTF	1.649	V
28	ITF	401.9	mA
29	PTF	0.000	deg
30	CJC	1.190	pF
31	VJC	160.1	mV
32	MJC	89.44	m
33	XCJC	130.0	m
34	TR	2.148	ns
35 (note 1)	CJS	0.000	F
36 (note 1)	VJS	750.0	mV
37 (note 1)	MJS	0.000	–
38	FC	785.9	m

Note

1. These parameters have not been extracted, the default values are shown.



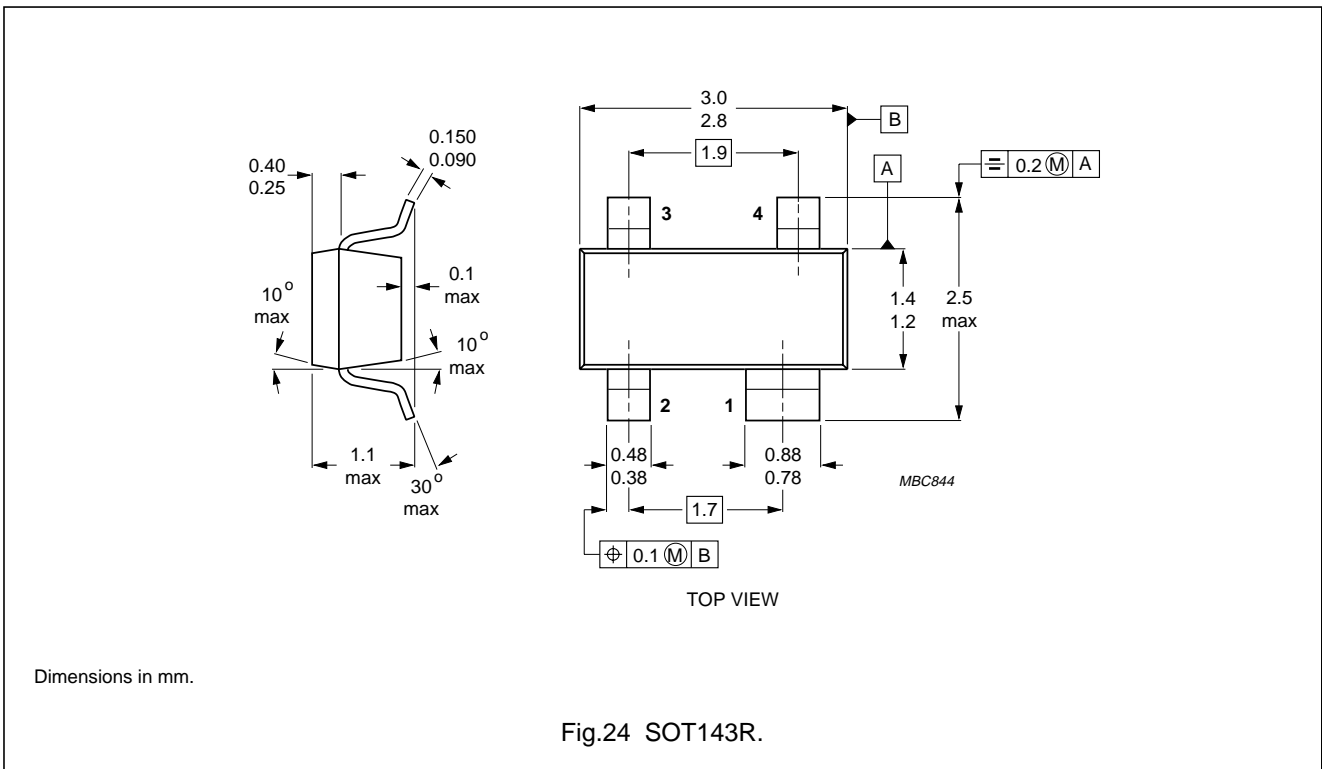
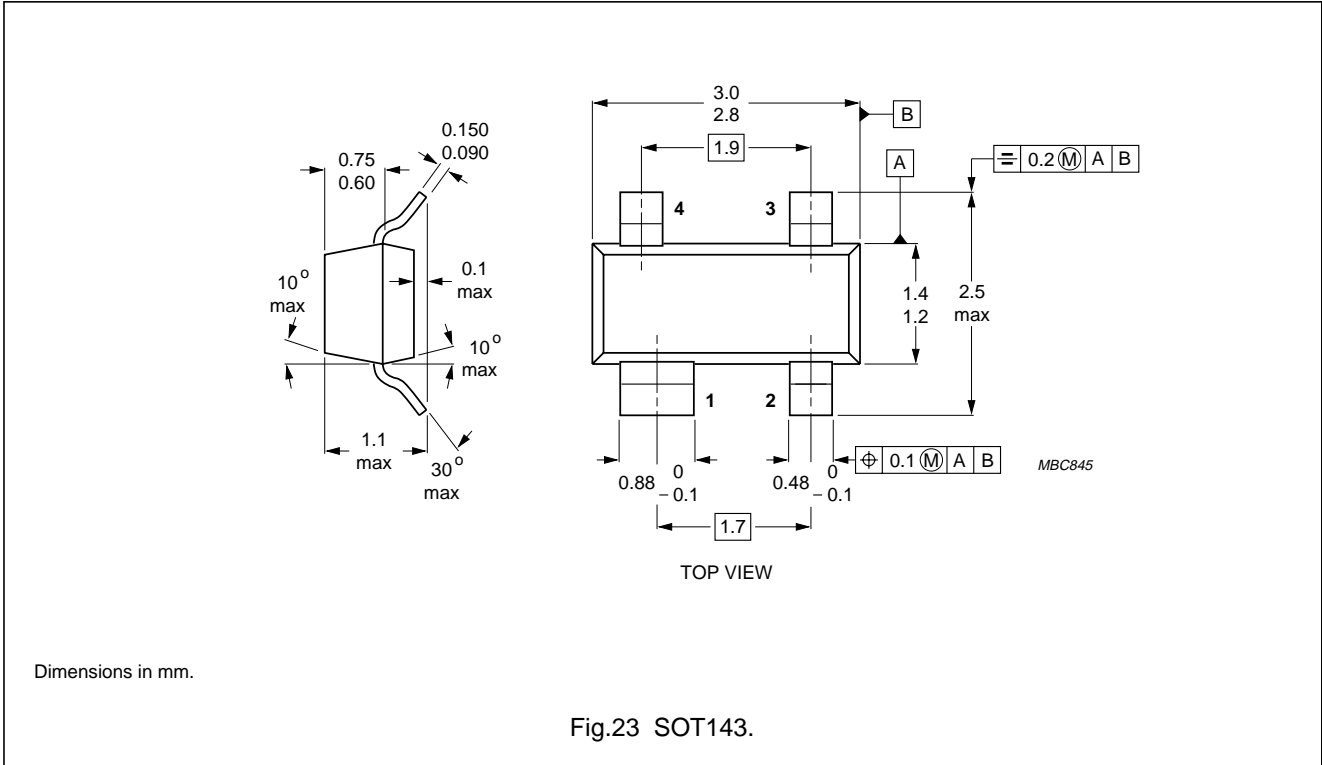
List of components (see Fig.22)

DESIGNATION	VALUE	UNIT
C _{be}	84	fF
C _{cb}	17	fF
C _{ce}	191	fF
L1	0.12	nH
L2	0.21	nH
L3	0.06	nH
L _B	0.95	nH
L _E	0.40	nH

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PACKAGE OUTLINES



NPN 7 GHz wideband transistor

BFG197; BFG197/X;
BFG197/XR**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.